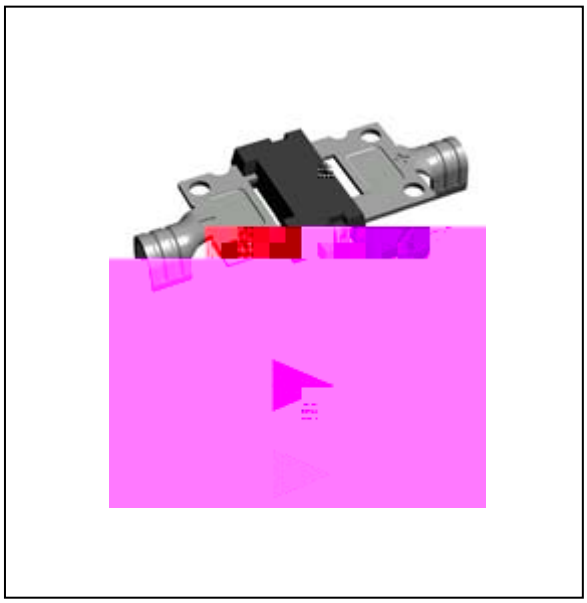
GFMK6045C

Schottky Bypass Diode Module



Features

- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability

Typical Applications

Photovoltaic solar cell protection schottky rectifier

Mechanical Data

- **Package:** GF025

Molding compound meets UL 94 V-0 flammability rating,

- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD 22-B102
- **Polarity:** As marked

■Maximum Ratings (T_a=25℃ Unless otherwise specified)

Device marking code			GFMK6045C
Repetitive Peak Reverse Voltage	V_{RRM}	V	45
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25	I_O	A	60
Surge(Non-repetitive)Forward Current @60Hz sine wave, 1 cycle, T_j=25	I_{FSM}	A	700
Current Squared Time @1ms≤t<8.3ms Tj=25 , Rating of per diode	I^2t	A^2S	2030

Note

(1) Meets the requirements of IEC 61215 Ed. 2 bypass diode thermal test.

■Electrical Characteristics (T_a=25℃ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	GFMK6045C
Maximum instantaneous forward voltage drop per diode	V_F	V	I_{FM}=60A	0.51
Maximum DC reverse current at rated DC blocking voltage per diode	I_{RRM1}	mA	V_{RM}=V_{RRM} Ta=25	0.12
	I_{RRM2}	mA	V_{RM}=V_{RRM} Ta=100	18
	I_{RRM3}	mA	V_{RM}=V_{RRM} Ta=125	70

SYMBOL UNIT GFMK6045C

■Thermal Characteristics (Ta=25℃ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	GFMK6045C
Thermal Resistance（1）	RθJ-C	/W	1.5

Note

(1) Thermal resistance from Between junction and case, On glass-epoxi substrate.

■Ordering Information (Example)

PREFERRED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
GFMK6045C	Approximate 4.0	30	600	2400	Tube

■Characteristics (Typical)

FIG1:Io -Tc Curve